

N-Channel Enhancement Mode MOSFET

Feature

Pin Description

- 80V/100A
 $R_{DS(ON)}=4.1\text{ m } (\text{typ.})@V_{GS} = 10\text{V}$
- 100% Avalanche Tested
- Reliable and Rugged
- Halogen-Free Devices Available
(RoHS Compliant)

Applications

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Absolute Maximum Ratings

Symbol	Parameter		Rating	Unit
Common Ratings (Tc=25°C Unless Otherwise Noted)				
V _{DSS}	Drain-Source Voltage		80	V
V _{GSS}	Gate-Source Voltage		20	V
T _J	Junction Temperature Range		-55 to 175	°C
T _{STG}	Storage Temperature Range		-55 to 175	°C
I _S	Source Current-Continuous(Body Diode)	Tc=25°C	100	A
Mounted on Large Heat Sink				
I _{DM}	Pulsed Drain Current *	Tc=25°C	**410	A
I _D	Continuous Drain Current	Tc=25°C	100	A
		Tc=100°C	70.7	A
P _D	Maximum Power Dissipation	Tc=25°C	93.7	W
		Tc=100°C	46.8	W
R _{θJC}	Thermal Resistance, Junction-to-Case		1.6	°C/W
R _{θJA}	Thermal Resistance, Junction-to-Ambient **		35	°C/W
E _{AS}	SinglePulsed-Avalanche Energy ***	L=0.3mH	350***	mJ

Note: * Repetitive rating pulse width limited by max.junction temperature.
 ** Surface mounted on 1in2 FR-4 board.
 *** Limited by T_{Jmax}, starting T_J=25°C, L = 0.3mH, R_θ= 25Ω, V_{GS}=10V.

Electrical Characteristics(Tc =25°C Unless Otherwise Noted)

Symbol	Parameter	Test Conditions	HYG050N08NS1			Unit
			Min	Typ.	Max	
Static Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _{DS} = 250 A	80	-	-	V
I _{DSS}	Drain-to-Source Leakage Current					

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Electrical Characteristics (Cont.) (Tc =25°C Unless Otherwise Noted)

Symbol	Parameter	Test Conditions	HYG050N08NS1			Unit
			Min	Typ.	Max	
Dynamic Characteristics						
R _G	Gate Resistance	V _{GS} =0V, V _{DS} =0V, F=1MHz	-	2.6	-	Ω
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} = 25V, Frequency=1.0MHz	-	4280	-	pF
C _{oss}	Output Capacitance		-	1770	-	
C _{rss}	Reverse Transfer Capacitance		-	25	-	
t _{d(ON)}	Turn-on Delay Time	V _{DD} = 40V, R _G =4.0 I _{DS} = 50A, V _{GS} = 10V	-	17	-	ns
T _r	Turn-on Rise Time		-	87	-	
t _{d(OFF)}	Turn-off Delay Time		-	47	-	
T _f	Turn-off Fall Time		-	101	-	
Gate Charge Characteristics						
Q _g	Total Gate Charge					Λ

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Typical Operating Characteristics

Figure 1: Power Dissipation

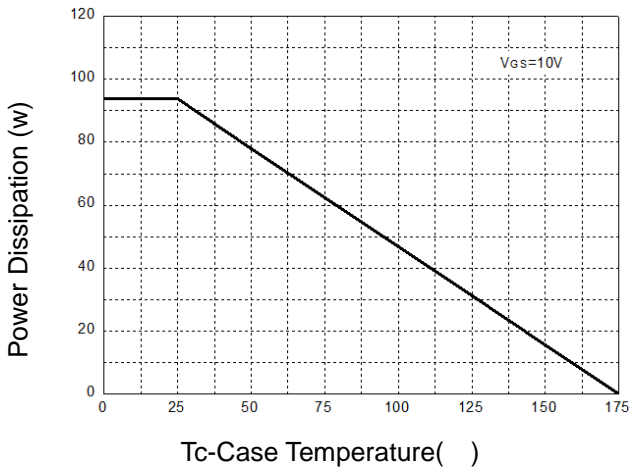


Figure 2: Drain Current

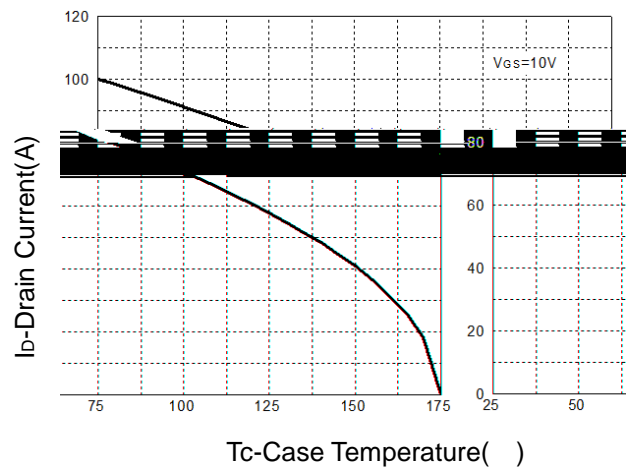


Figure 3: Safe Operation Area

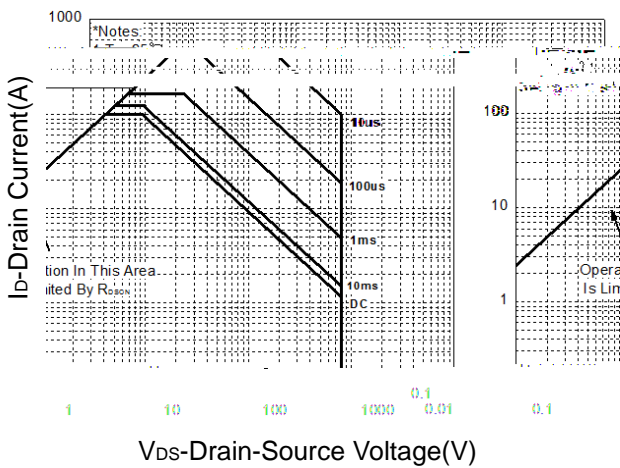


Figure 4: Thermal Transient Impedance

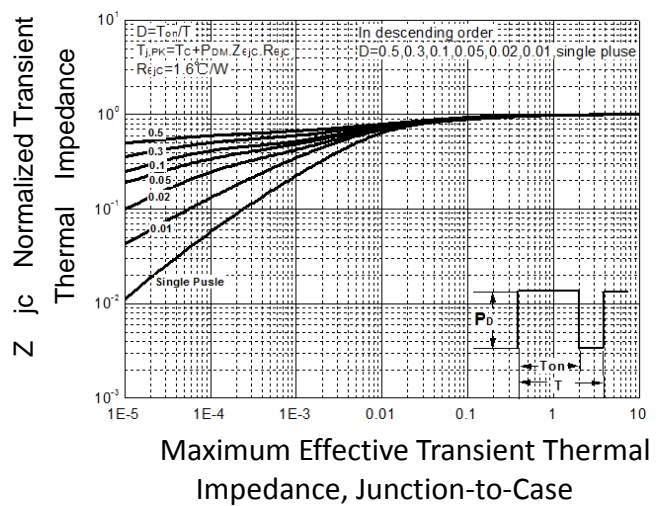


Figure 5: Output Characteristics

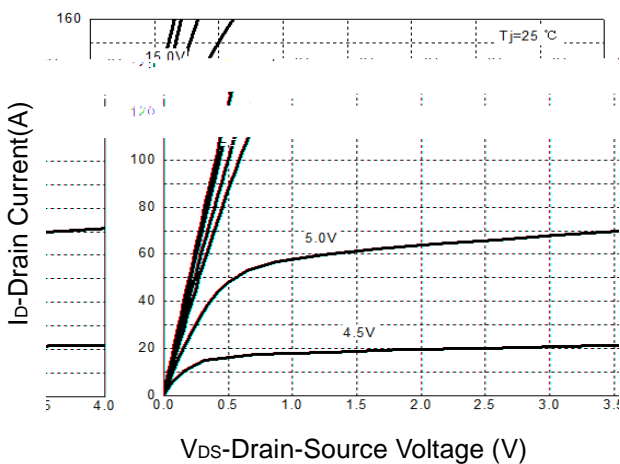
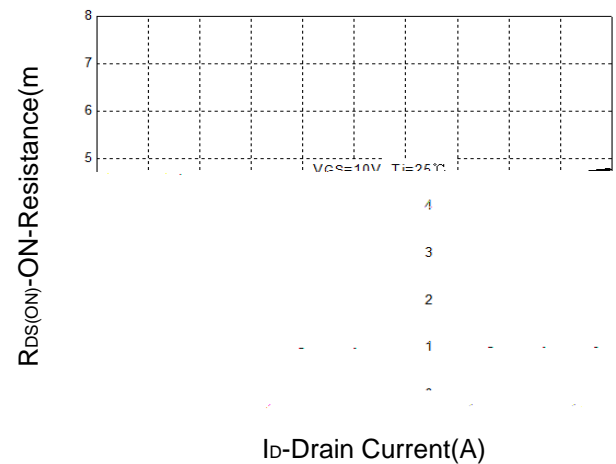


Figure 6: Drain-Source On Resistance



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Typical Operating Characteristics(Cont.)

Figure 7: On-Resistance vs. Temperature

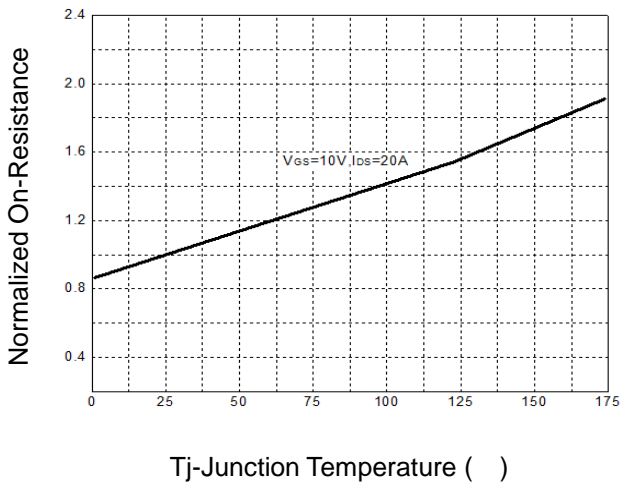


Figure 8: Source-Drain Diode Forward

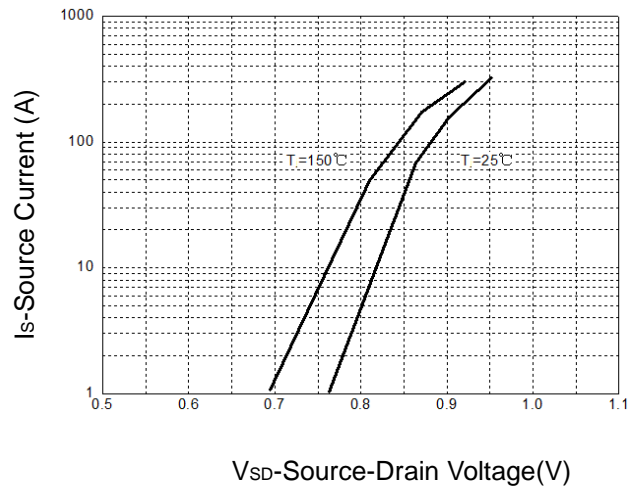


Figure 9: Capacitance Characteristics

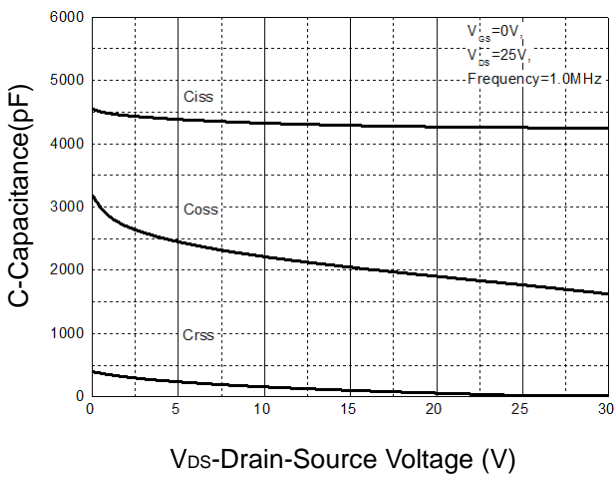
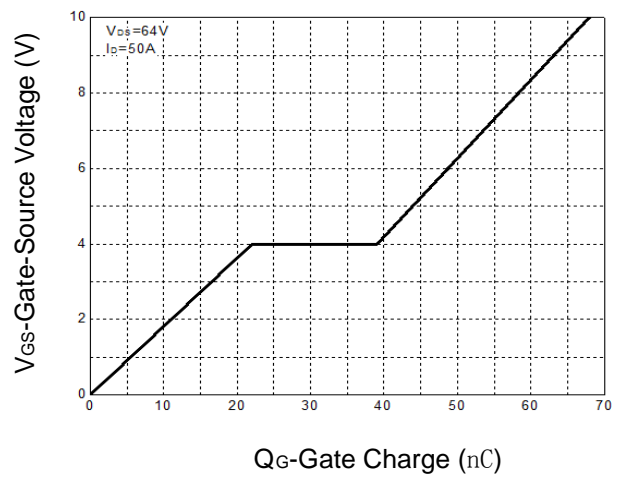
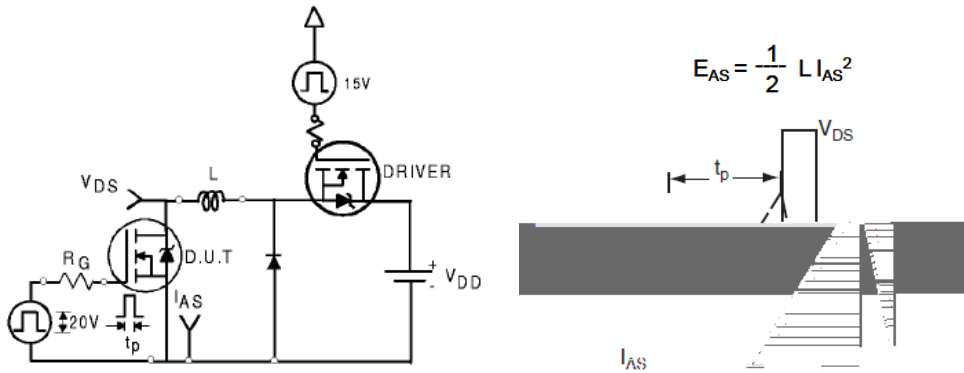


Figure 10: Gate Charge Characteristics

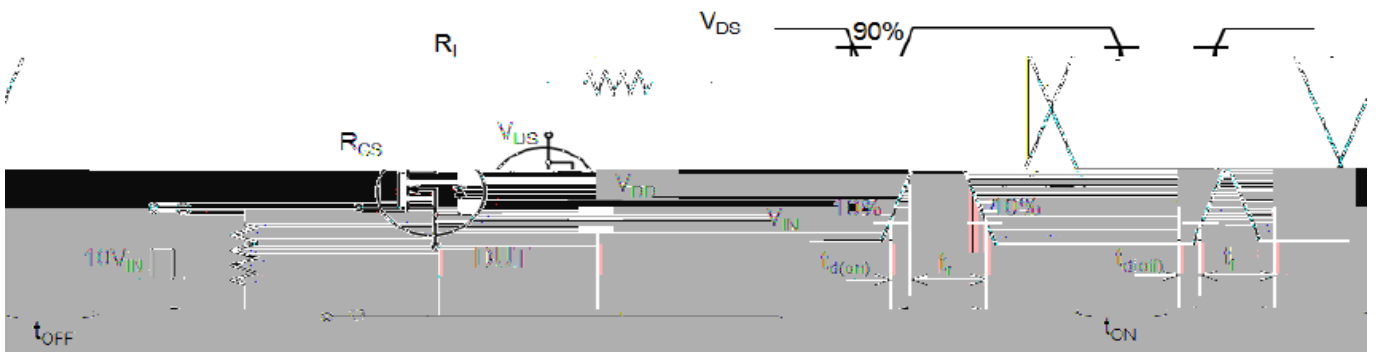


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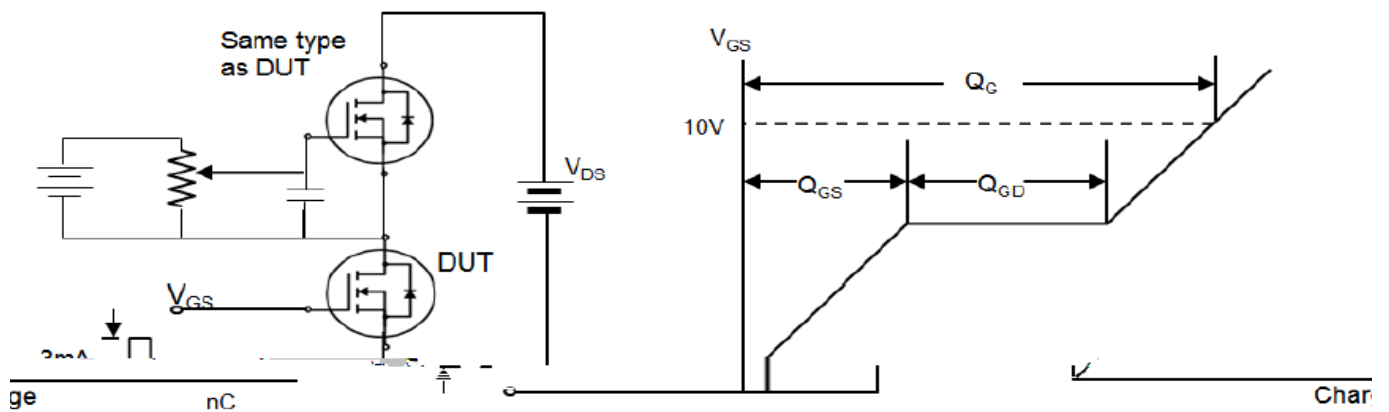
Avalanche Test Circuit



Switching Time Test Circuit



Gate Charge Test Circuit



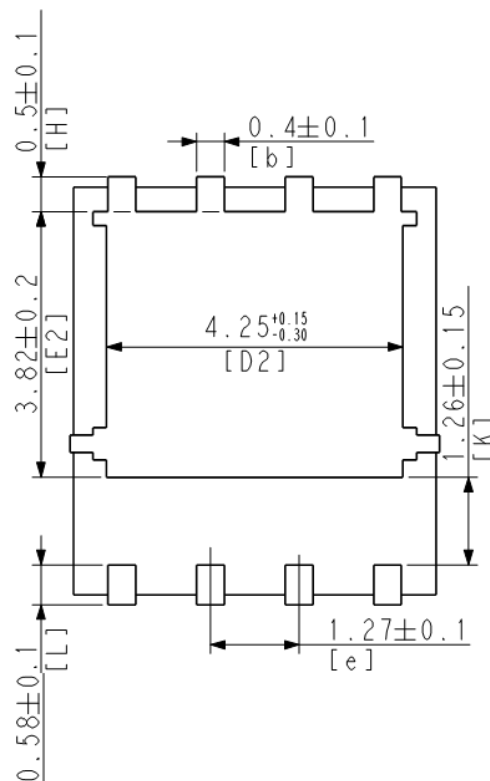
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Device Per Unit

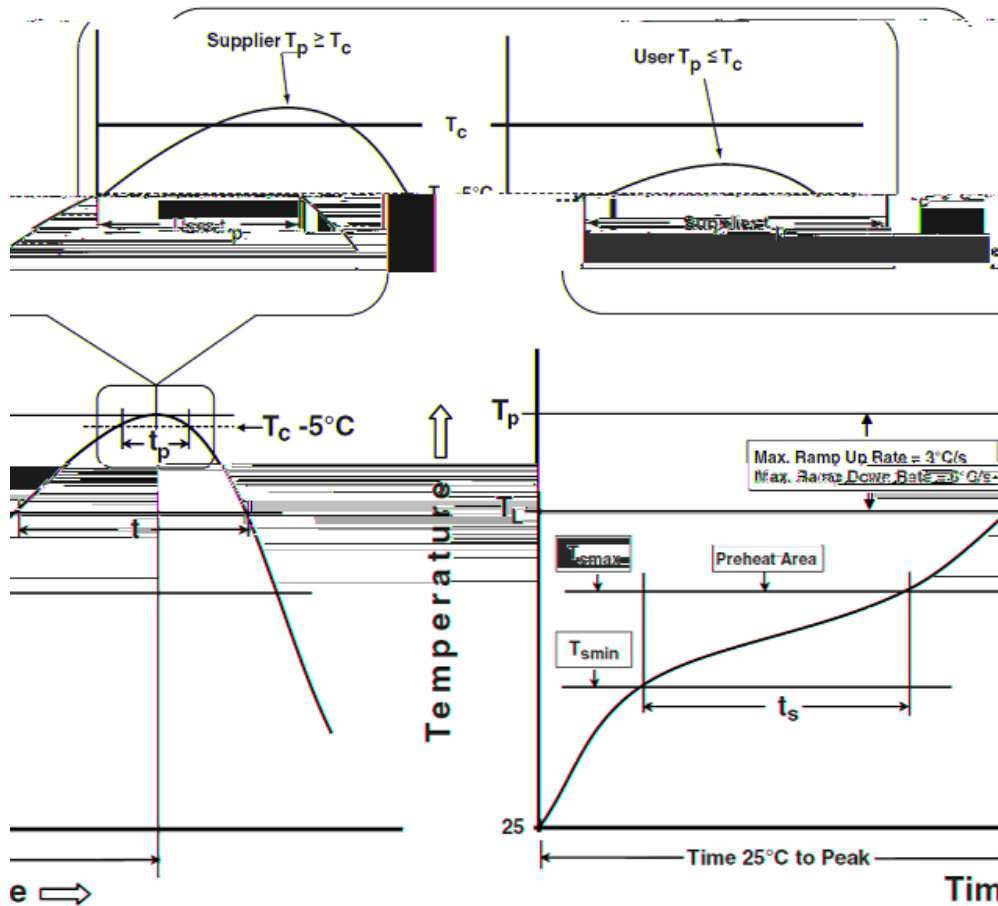
Package Type	Unit	Quantity
PPAK5*6-8L	Reel	5000

Package Information

PPAK5*6-8L



Classification Profile



Classification Reflow Profiles

Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Preheat & Soak		
Temperature min (T_{smin})	100 °C	150 °C
Temperature max (T_{smax})	150 °C	200 °C
Time (T_{smin} to T_{smax}) (t_s)	60-120 seconds	60-120 seconds
Average ramp-up rate (T_{smax} to T_p)	3 °C/second max.	3°C/second max.
Liquidous temperature (T_L)	183 °C	217 °C
Time at liquidous (t_L)	60-150 seconds	60-150 seconds
Peak package body Temperature (T_p)*	See Classification Temp in table 1	See Classification Temp in table 2
Time (t_p)** within 5°C of the specified classification temperature (T_c)	20** seconds	30** seconds
Average ramp-down rate (T_p to T_{smax})	6 °C/second max.	6 °C/second max.
Time 25°C to peak temperature	6 minutes max.	8 minutes max.

*Tolerance for peak profile Temperature (T_p) is defined as a supplier minimum and a user maximum.

** Tolerance for time at peak profile temperature (t_p) is defined as a supplier minimum and a user maximum.

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Table 1. SnPb Eutectic Process Classification Temperatures (Tc)

Package Thickness	Volume mm <350	Volume mm 350
2.5 mm	235 °C	220 °C
	220 °C	220 °C

Table 2. Pb-free Process Classification Temperatures (Tc)

Package Thickness	Volume mm <350	Volume mm 350-2000	Volume mm 2000
<1.6 mm	260 °C	260 °C	260 °C
1.6 mm 2.5 mm	260 °C	250 °C	245 °C
2.5 mm	250 °C	245 °C	245 °C

Reliability Test Program

Test item	Method	Description
SOLDERABILITY	JESD-22, B102	5 Sec, 245°C
PRECON	JESD-22, A113	30°C/60%/192Hrs